

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A method for producing an epitaxial wafer by depositing a film of epitaxial layer through an epitaxial growth over a top surface of a silicon wafer, said method comprising:

 a first cleaning step for cleaning a top and a back surfaces of a silicon wafer with a SC-1 liquid and a SC-2 liquid;

 a second cleaning step, after said first cleaning step, for cleaning said back surface of said silicon wafer to be a water repellent surface; and

 a third cleaning step for cleaning said top surface of said silicon wafer to be a water repellent surface, wherein

 after said three steps of cleaning having been finished, a film of epitaxial layer is deposited through an epitaxial growth over said top surface of said silicon wafer.

2. (Original) A method for producing an epitaxial wafer in accordance with claim 1, in which said second and said third cleaning steps are performed simultaneously.

3. (Original) A method for producing an epitaxial wafer in accordance with claim 1, in which a contact angle of said water repellent surface is 30° or greater.

4. (Original) A method for producing an epitaxial wafer in accordance with claim 2, wherein a contact angle of said water repellent surface is 30° or greater.

5. (Currently Amended) A method for producing an epitaxial wafer in accordance with claim 1 ~~any one of claim 1 to 4~~, in which said second and said third cleaning steps provide the cleaning by using at least either one of HF solution or BHF solution.

6. (Original) A method for producing an epitaxial wafer by depositing a film of epitaxial layer through an epitaxial growth over a top surface of a silicon wafer, said method comprising:

 a fourth cleaning step for cleaning a top and a back surfaces of a silicon wafer with a SC-1 liquid and a SC-2 liquid;

 a fifth cleaning step, after said fourth cleaning step, for cleaning said back surface of said silicon wafer to be a water repellent surface; and

 a sixth cleaning step for cleaning said top surface of said silicon wafer to be a hydrophilic surface, wherein

after said three steps of cleaning having been finished, a film of epitaxial layer is deposited through an epitaxial growth over said top surface of said silicon wafer.

7. (Original) A method for producing an epitaxial wafer in accordance with claim 6, in which said fifth and said sixth cleaning steps are performed simultaneously.

8. (Original) A method for producing an epitaxial wafer in accordance with claim 6, in which a contact angle of said hydrophilic surface is 20° or smaller and a contact angle of said water repellent surface is 30° or greater.

9. (Original) A method for producing an epitaxial wafer in accordance with claim 7, in which a contact angle of said hydrophilic surface is 20° or smaller and a contact angle of said water repellent surface is 30° or greater.

10. (Currently Amended) A method for producing an epitaxial wafer in accordance with claim 6 ~~any one of claim 6 to 9~~, in which said sixth cleaning step provides a cleaning by a combination of a sponge brush with a purified water.

11. (Original) An epitaxial wafer with a film of epitaxial layer deposited through an epitaxial growth over a top surface of a silicon wafer, said wafer being produced by a method comprising the steps of:

cleaning a top and a back surfaces of a silicon wafer by using a SC-1 liquid and a SC-2 liquid;

subsequently processing said back surface of said silicon wafer into a water repellent surface;

further processing said top surface of said silicon wafer into a water repellent surface; and

then depositing said film of epitaxial layer through an epitaxial growth over said top surface of said silicon wafer.

12. (Original) An epitaxial wafer with a film of epitaxial layer deposited through an epitaxial growth over a top surface of a silicon wafer, said wafer being produced by a method comprising the steps of:

cleaning a top and a back surfaces of a silicon wafer by using a SC-1 liquid and a SC-2 liquid;

subsequently processing said back surface of said silicon wafer into a water repellent surface;

further processing said top surface of said silicon wafer into a hydrophilic surface; and

then depositing a film of epitaxial layer through an epitaxial growth over said top surface of said silicon wafer.

13. (New) A method for producing an epitaxial wafer in accordance with claim 2, in which said second and said third cleaning steps provide the cleaning by using at least either one of HF solution or BHF solution.

14. (New) A method for producing an epitaxial wafer in accordance with claim 3, in which said second and said third cleaning steps provide the cleaning by using at least either one of HF solution or BHF solution.

15. (New) A method for producing an epitaxial wafer in accordance with claim 4, in which said second and said third cleaning steps provide the cleaning by using at least either one of HF solution or BHF solution.

16. (New) A method for producing an epitaxial wafer in accordance with claim 7, in which said sixth cleaning step provides a cleaning by a combination of a sponge brush with a purified water.

17. (New) A method for producing an epitaxial wafer in accordance with claim 8, in which said sixth cleaning step provides a cleaning by a combination of a sponge brush with a purified water.

18. (New) A method for producing an epitaxial wafer in accordance with claim 9, in which said sixth cleaning step provides a cleaning by a combination of a sponge brush with a purified water.